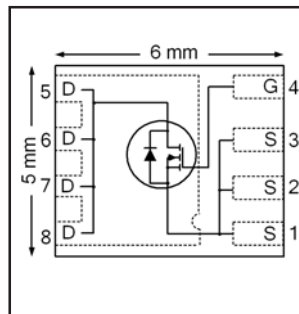


HEXFET® Power MOSFET

V_{DS}	150	V
$R_{DS(on)}$ max (@ $V_{GS} = 10V$)	31	mΩ
Q_g (typical)	36	nC
R_G (typical)	1.7	Ω
I_D (@ $T_{mb} = 25^\circ C$)	44	A



Applications

- Primary Side Synchronous Rectification
- Inverters for DC Motors
- DC-DC Brick Applications
- Boost Converters

Features and Benefits

Features

Low $R_{DS(on)}$ (< 31 mΩ)
Low Thermal Resistance to PCB (<0.8°C/W)
100% R_g tested
Low Profile (<0.9 mm)
Industry-Standard Pinout
Compatible with Existing Surface Mount Techniques
RoHS Compliant Containing no Lead, no Bromide and no Halogen
MSL1, Industrial Qualification

Benefits

Lower Conduction Losses
Increased Power Density
Increased Reliability
Increased Power Density
Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

results in
⇒

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFH5015PbF	PQFN 5mm x 6mm	Tape and Reel	4000	IRFH5015TRPbF

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	150	V
V_{GS}	Gate-to-Source Voltage	± 20	
I_D @ $T_A = 25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	10	A
I_D @ $T_A = 70^\circ C$	Continuous Drain Current, V_{GS} @ 10V	8.2	
I_D @ $T_{mb} = 25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	44	
I_D @ $T_{mb} = 100^\circ C$	Continuous Drain Current, V_{GS} @ 10V	28	
I_{DM}	Pulsed Drain Current ①	220	
P_D @ $T_A = 25^\circ C$	Power Dissipation ⑤	3.6	W
P_D @ $T_{mb} = 25^\circ C$	Power Dissipation ⑤	156	
	Linear Derating Factor ⑤	0.029	W/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Notes ① through ⑤ are on page 9

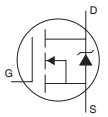
Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	150	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.12	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1.0\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	25.5	31	m Ω	$V_{GS} = 10V, I_D = 34A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 150\mu A$
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-12	—	mV/ $^\circ\text{C}$	
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 150V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 150V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
g_{fs}	Forward Transconductance	38	—	—	S	$V_{DS} = 50V, I_D = 34A$
Q_g	Total Gate Charge	—	36	54	nC	$V_{DS} = 75V$ $V_{GS} = 10V$ $I_D = 34A$
Q_{gs1}	Pre-V _{th} Gate-to-Source Charge	—	13	—		
Q_{gs2}	Post-V _{th} Gate-to-Source Charge	—	4.6	—		
Q_{gd}	Gate-to-Drain Charge	—	11	—		
Q_{godr}	Gate Charge Overdrive	—	7.4	—		
Q_{sw}	Switch Charge ($Q_{gs2} + Q_{gd}$)	—	15.6	—	nC	$V_{DS} = 16V, V_{GS} = 0V$
Q_{oss}	Output Charge	—	14	—		
R_G	Gate Resistance	—	1.7	—	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	9.4	—	ns	$V_{DD} = 75V, V_{GS} = 10V$ $I_D = 34A$ $R_G = 1.3\Omega$
t_r	Rise Time	—	9.7	—		
$t_{d(off)}$	Turn-Off Delay Time	—	14	—		
t_f	Fall Time	—	3.4	—	pF	$V_{GS} = 0V$ $V_{DS} = 50V$ $f = 1.0\text{MHz}$
C_{iss}	Input Capacitance	—	2300	—		
C_{oss}	Output Capacitance	—	205	—		
C_{rss}	Reverse Transfer Capacitance	—	47	—		

Avalanche Characteristics

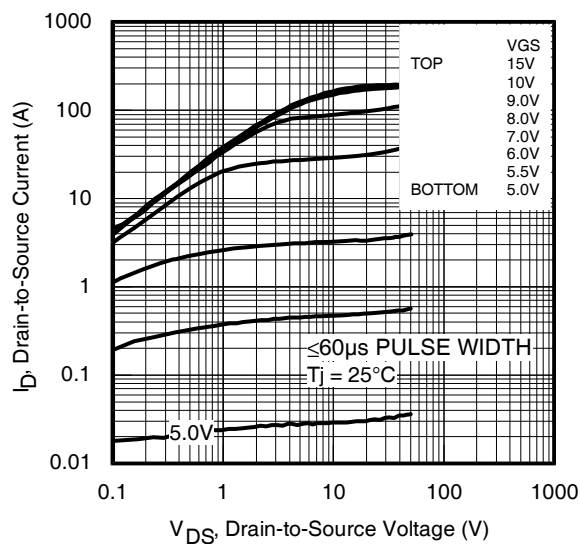
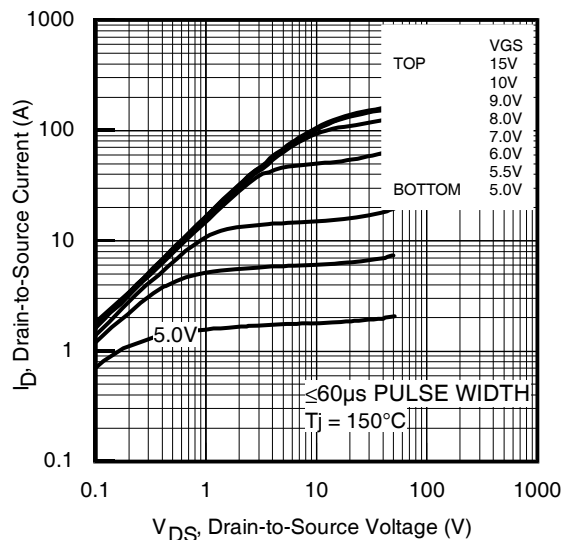
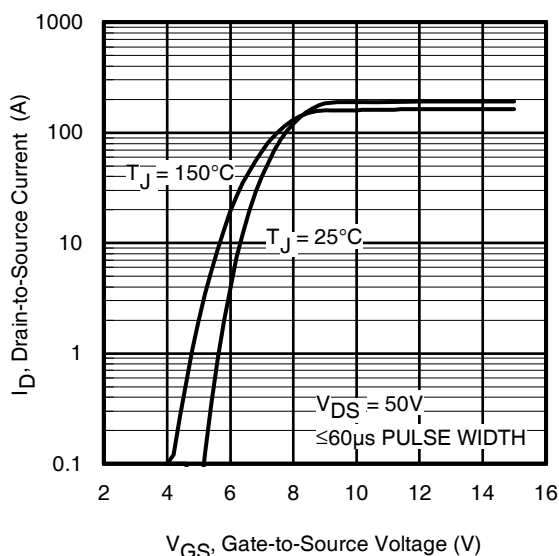
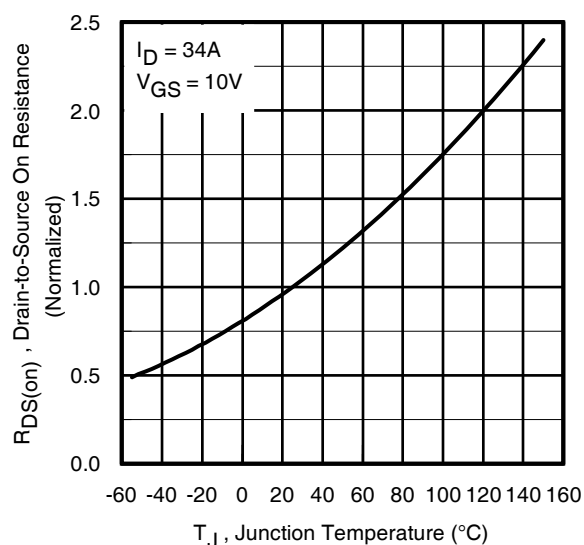
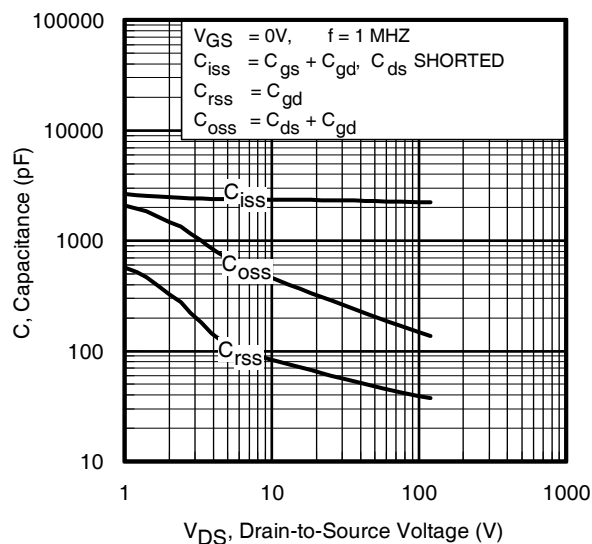
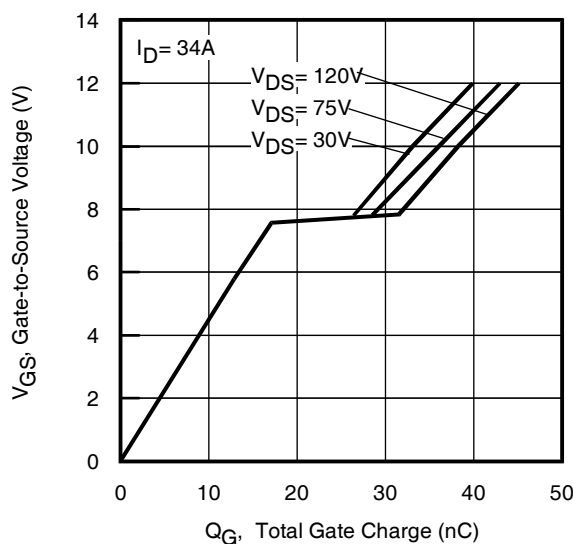
	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	230	mJ
I_{AR}	Avalanche Current ①	—	34	A

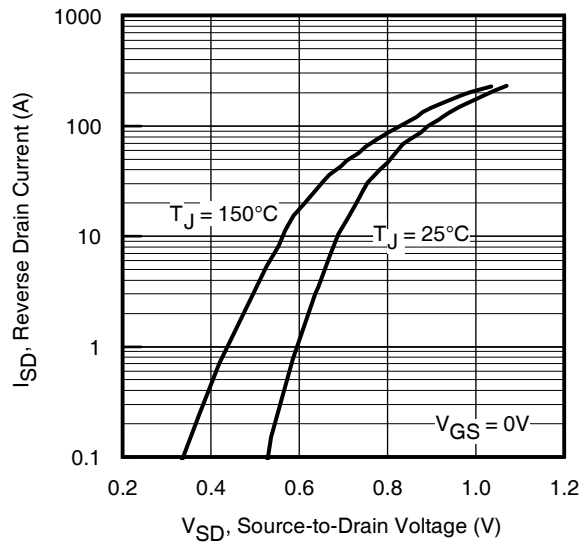
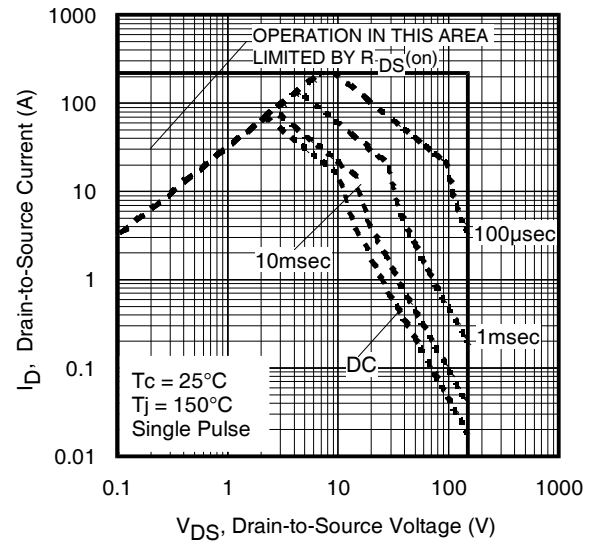
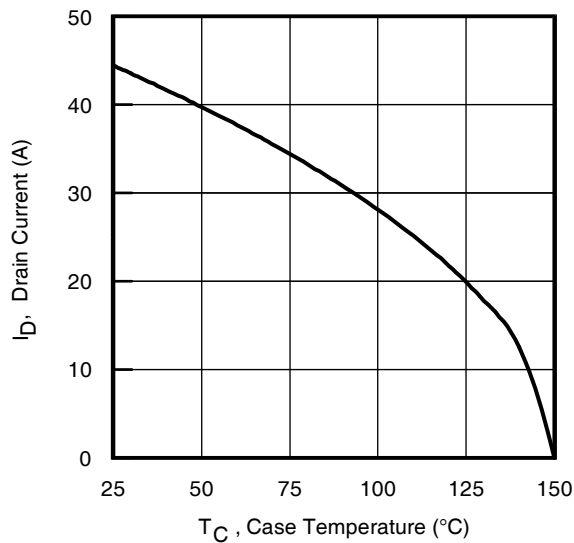
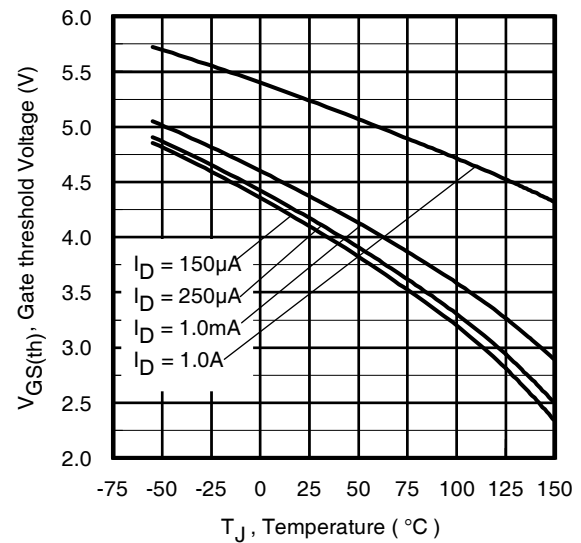
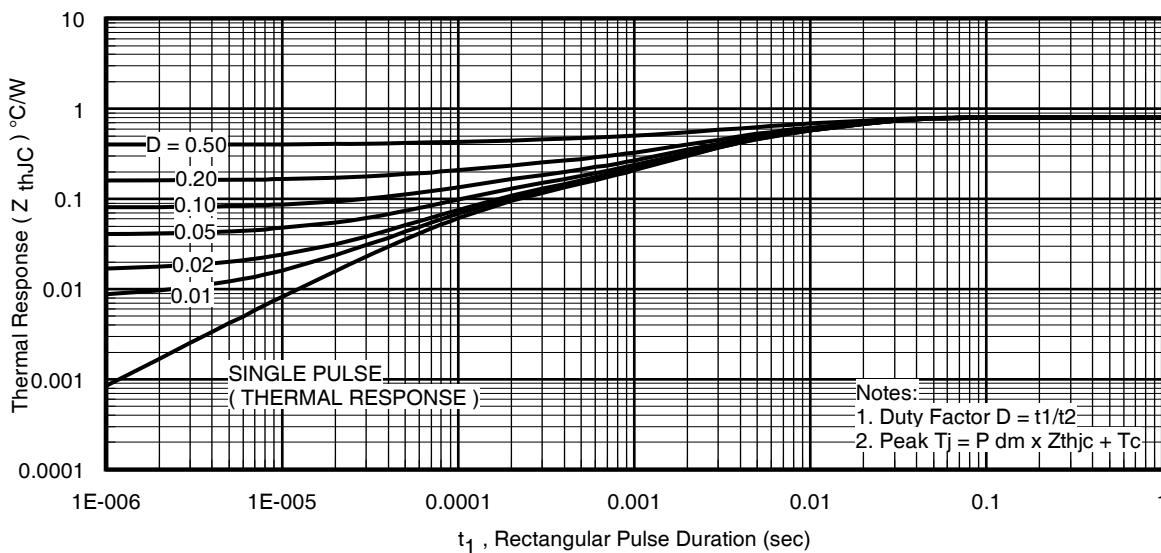
Diode Characteristics

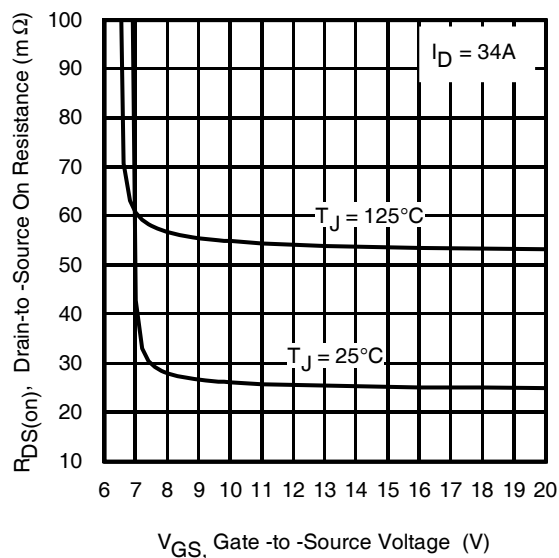
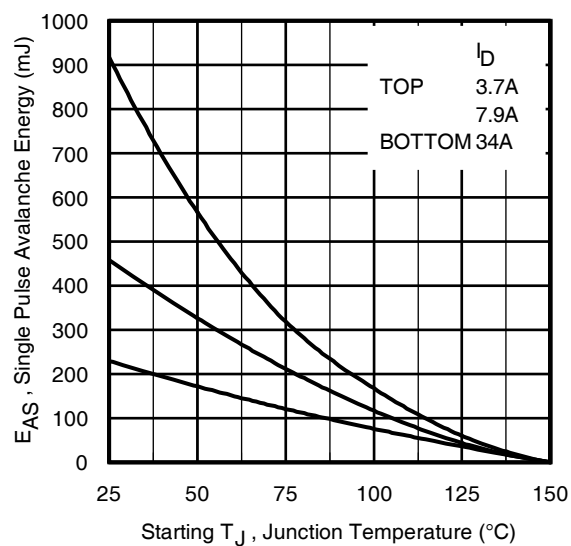
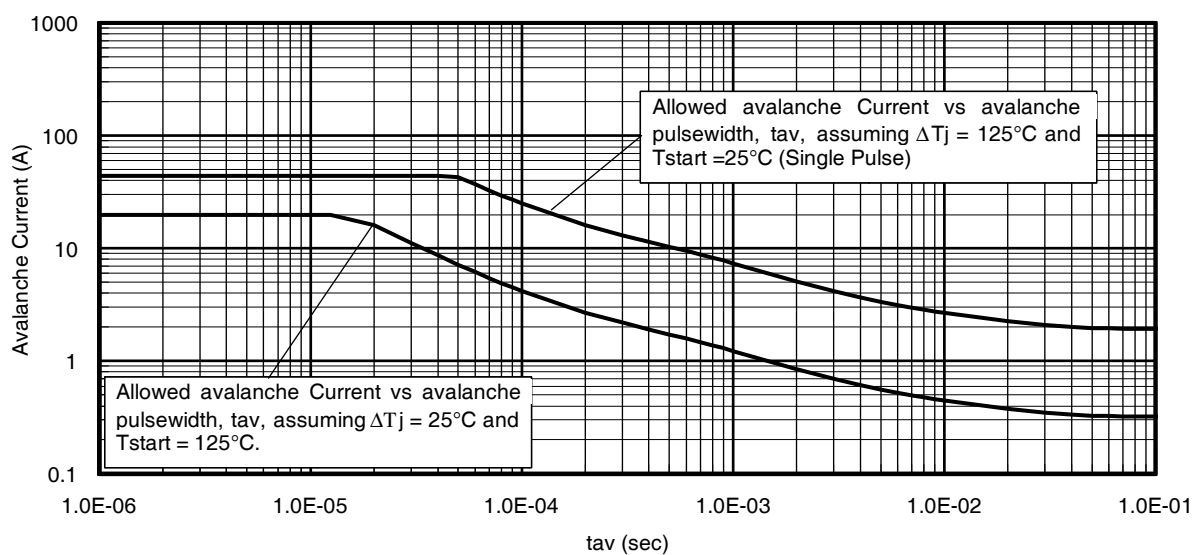
	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	56	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	220		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 34A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	52	78	ns	$T_J = 25^\circ\text{C}, I_F = 34A, V_{DD} = 75V$
Q_{rr}	Reverse Recovery Charge	—	550	825	nC	$di/dt = 500A/\mu s$ ③
t_{on}	Forward Turn-On Time	Time is dominated by parasitic Inductance				

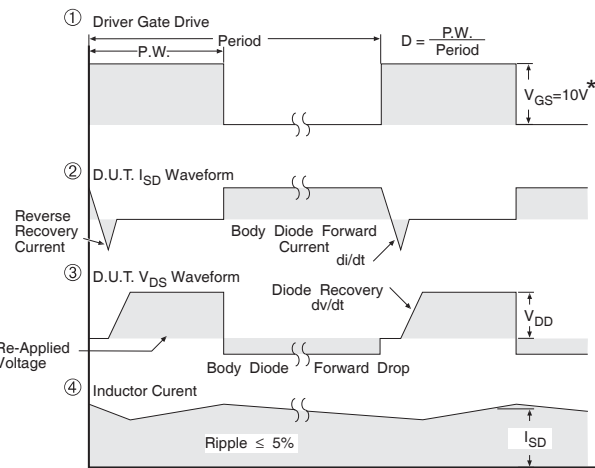
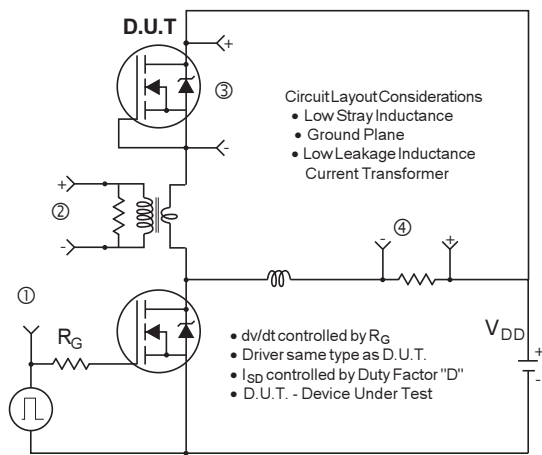
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC-mb}$	Junction-to-Mounting Base	0.5	0.8	$^\circ\text{C/W}$
$R_{\theta JC}$ (Top)	Junction-to-Case ④	—	15	
$R_{\theta JA}$	Junction-to-Ambient ⑤	—	35	
$R_{\theta JA} (<10s)$	Junction-to-Ambient ⑤	—	22	


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance vs. Temperature

Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage


Fig 7. Typical Source-Drain Diode Forward Voltage

Fig 8. Maximum Safe Operating Area

Fig 9. Maximum Drain Current vs. Case Temperature

Fig 10. Threshold Voltage vs. Temperature

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Mounting Base


Fig 12. On-Resistance vs. Gate Voltage

Fig 13. Maximum Avalanche Energy vs. Drain Current

Fig 14. Typical Avalanche Current vs. Pulsewidth



* $V_{GS} = 5V$ for Logic Level Devices

Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

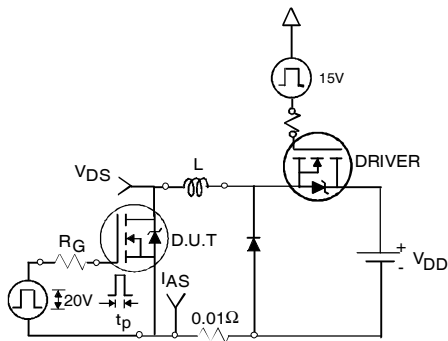


Fig 16a. Unclamped Inductive Test Circuit

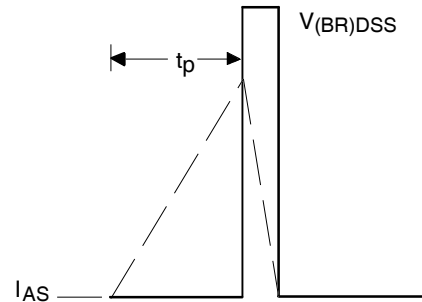


Fig 16b. Unclamped Inductive Waveforms

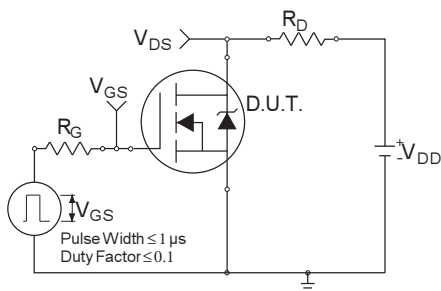


Fig 17a. Switching Time Test Circuit

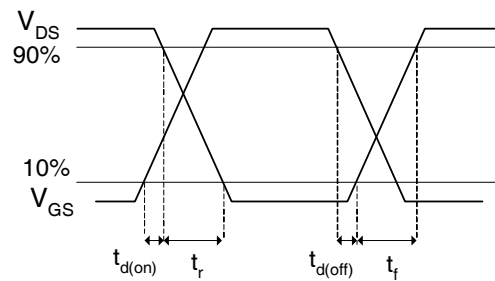


Fig 17b. Switching Time Waveforms

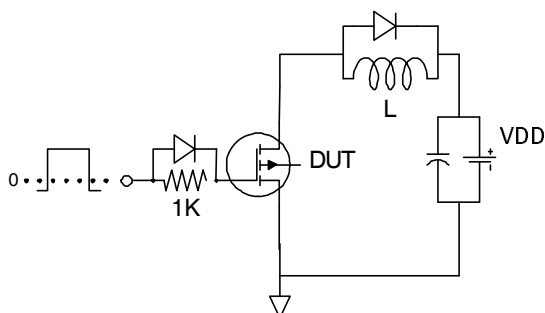


Fig 18a. Gate Charge Test Circuit

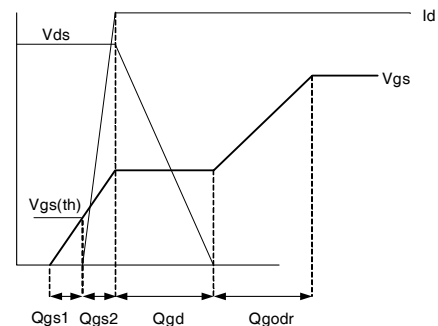
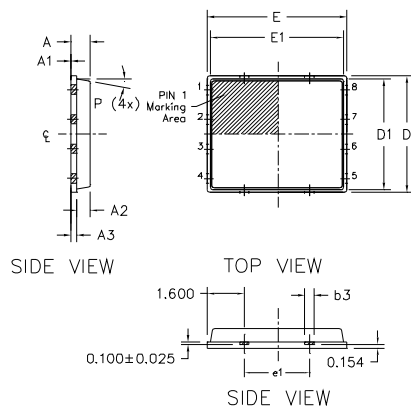


Fig 18b. Gate Charge Waveform

PQFN 5x6 Outline "B" Package Details

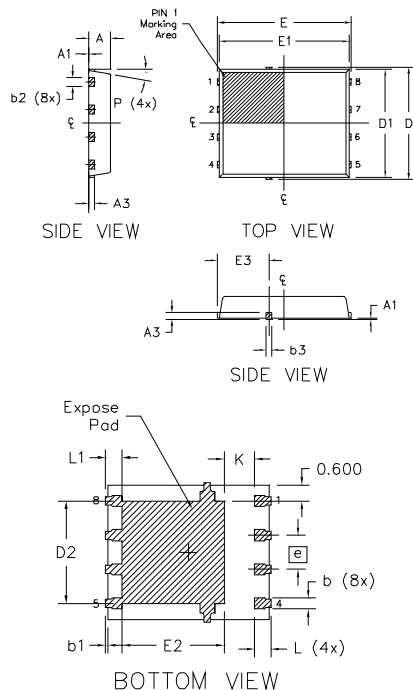


DIM SYMBOL	MILLIMETERS		INCH	
	MIN	MAX	MIN	MAX
A	0.800	0.900	0.0315	0.0543
A1	0.000	0.050	0.0000	0.0020
A3	0.200	REF	0.0079	REF
b	0.350	0.470	0.0138	0.0185
b1	0.025	0.125	0.0010	0.0049
b2	0.210	0.410	0.0083	0.0161
b3	0.150	0.450	0.0059	0.0177
D	5.000	BSC	0.1969	BSC
D1	4.750	BSC	0.1870	BSC
D2	4.100	4.300	0.1614	0.1693
E	6.000	BSC	0.2362	BSC
E1	5.750	BSC	0.2264	BSC
E2	3.380	3.780	0.1331	0.1488
e	1.270	REF	0.0500	REF
e1	2.800	REF	0.1102	REF
K	1.200	1.420	0.0472	0.0559
L	0.710	0.900	0.0280	0.0354
P	0°	12°	0°	12°
R	0.200	REF	0.0079	REF
R2	0.150	0.200	0.0059	0.0079

Note:

1. Dimensions and tolerancing confirm to ASME Y14.5M-1994
2. Dimension L represents terminal full back from package edge up to 0.1mm is acceptable
3. Coplanarity applies to the expose Heat Slug as well as the terminal
4. Radius on terminal is Optional

PQFN 5x6 Outline "G" Package Details



DIM SYMBOL	MILLIMETERS		INCH	
	MIN.	MAX.	MIN.	MAX.
A	0.950	1.050	0.0374	0.0413
A1	0.000	0.050	0.0000	0.0020
A3	0.254	REF	0.0100	REF
b	0.310	0.510	0.0122	0.0201
b1	0.025	0.125	0.0010	0.0049
b2	0.210	0.410	0.0083	0.0161
b3	0.180	0.450	0.0071	0.0177
D	5.150	BSC	0.2028	BSC
D1	5.000	BSC	0.1969	BSC
D2	3.700	3.900	0.1457	0.1535
E	6.150	BSC	0.2421	BSC
E1	6.000	BSC	0.2362	BSC
E2	3.560	3.760	0.1402	0.1488
E3	2.270	2.470	0.0894	0.0972
e	1.27	REF	0.050	REF
K	0.830	1.400	0.0327	0.0551
L	0.510	0.710	0.0201	0.0280
L1	0.510	0.710	0.0201	0.0280
P	10 deg	12 deg	0 deg	12 deg

Note:

1. Dimensions and tolerancing confirm to ASME Y14.5M-1994
2. Dimension L represents terminal full back from package edge up to 0.1mm is acceptable
3. Coplanarity applies to the expose Heat Slug as well as the terminal
4. Radius on terminal is Optional

For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136:

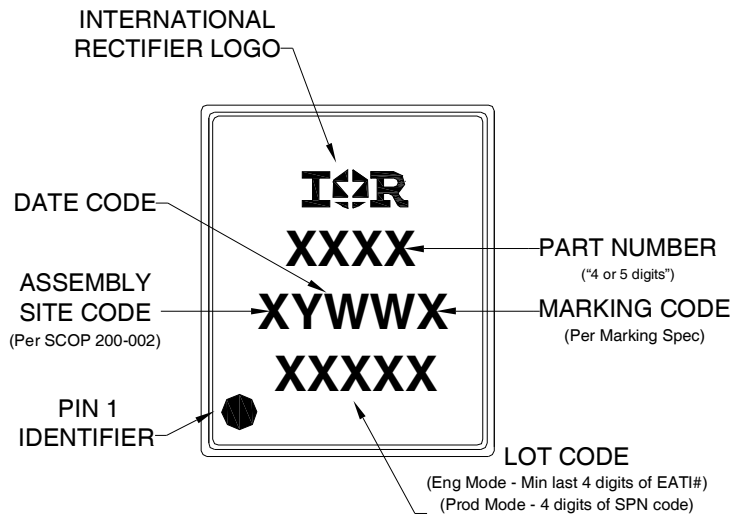
<http://www.irf.com/technical-info/appnotes/an-1136.pdf>

For more information on package inspection techniques, please refer to application note AN-1154:

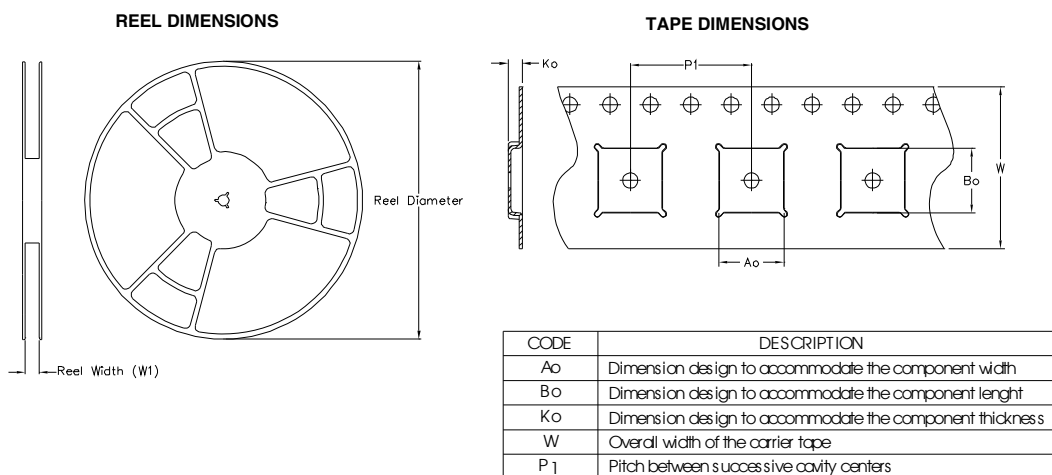
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Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

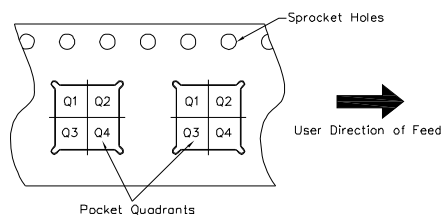
PQFN 5x6 Part Marking



PQFN 5x6 Tape and Reel



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Note: All dimension are nominal

Package Type	Reel Diameter (Inch)	QTY	Reel Width W1 (mm)	Ao (mm)	Bo (mm)	Ko (mm)	P1 (mm)	W (mm)	Pin 1 Quadrant
5 X 6 PQFN	13	4000	12.4	6.300	5.300	1.20	8.00	12	Q1

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

Qualification information[†]

Qualification level	Industrial ^{††} (per JEDEC JESD47F ^{†††} guidelines)	
Moisture Sensitivity Level	PQFN 5mm x 6mm	MSL1 (per JEDEC J-STD-020D ^{†††})
RoHS compliant	Yes	

[†] Qualification standards can be found at International Rectifier's web site

<http://www.irf.com/product-info/reliability>

^{††} Higher qualification ratings may be available should the user have such requirements.

Please contact your International Rectifier sales representative for further information:

<http://www.irf.com/whoto-call/salesrep/>

^{†††} Applicable version of JEDEC standard at the time of product release.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^{\circ}\text{C}$, $L = 0.41\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 34\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ R_G is measured at T_J of approximately 90°C .
- ⑤ When mounted on 1 inch square 2 oz copper pad on 1.5x1.5 in. board of FR-4 material.

Revision History

Date	Comment
4/28/2015	- Updated package outline for "option B" and added package outline for "option G" on page 7 - Updated tape and reel on page 8.
5/19/2015	- Updated package outline for "option G" on page 7. - Updated "IFX logo" on page 1 and page 9.

International
 Rectifier

AN INFINEON TECHNOLOGIES COMPANY

IR WORLD HEADQUARTERS: 101 N. Sepulveda Blvd., El Segundo, California 90245, USA

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